

SAMSUNG SEMICONDUCTOR INC 14E D 7964142 0006833 0 T-29-15

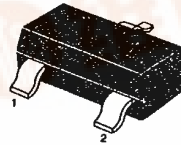
KSA1182**PNP EPITAXIAL SILICON TRANSISTOR****LOW FREQUENCY POWER AMPLIFIER**

• Complement to KSA2859

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-35	V
Collector-Emitter Voltage	V_{CE0}	-30	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-500	mA
Collector Dissipation	P_C	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$

SOT-23



1. Base 2. Emitter 3. Collector

3

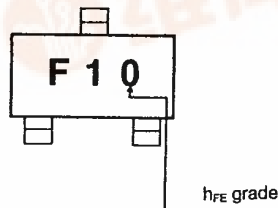
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=-35\text{V}, I_E=0$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
DC Current Gain	h_{FE1}	$V_{CE}=-1\text{V}, I_C=-100\text{mA}$	70		240	
	h_{FE2}	$V_{CE}=-6\text{V}, I_C=-400\text{mA}$	25			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-100\text{mA}, I_E=-10\text{mA}$		-0.1	-0.25	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C=-100\text{mA}, V_{CE}=-1\text{V}$		-0.8	-1.0	V
Current Gain-Bandwidth Product	f_T	$I_C=-20\text{mA}, V_{CE}=-6\text{V}$		200		MHz
Output Capacitance	C_{ob}	$V_{CB}=-6\text{V}, I_E=0$ $f=1\text{MHz}$		13		pF

 h_{FE} CLASSIFICATION

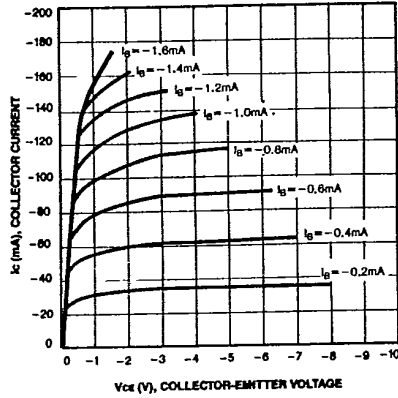
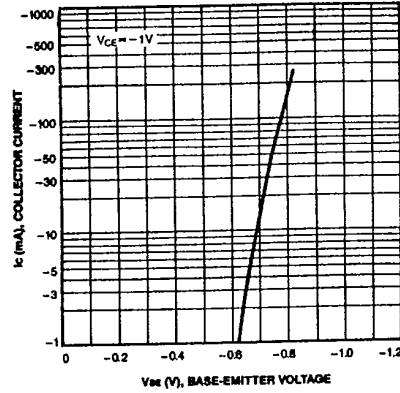
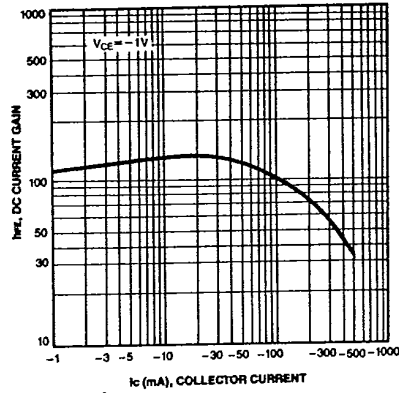
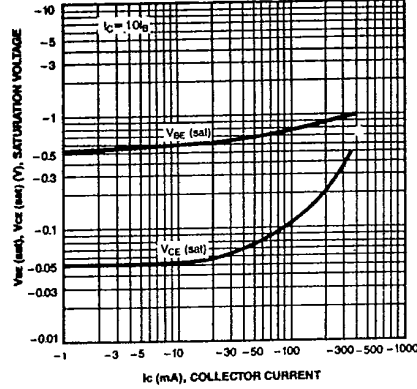
Classification	O	Y
$h_{FE}(1)$	70-140	120-240

Marking

 h_{FE} grade

KSA1182**PNP EPITAXIAL SILICON TRANSISTOR**

T-29-15

STATIC CHARACTERISTIC**BASE-EMITTER ON VOLTAGE****DC CURRENT GAIN****BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE****COLLECTOR OUTPUT CAPACITANCE**